



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Li Docket No.: 2003 P 54557 US
Serial No.: 10/771,075 Art Unit: 2811
Filed: February 3, 2004 Examiner: Gene M. Munson
For: Transistor with Doped Gate Dielectric

Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))

Date of Deposit: April 21, 2005

I hereby certify that the below listed correspondence is being deposited with the United States Postal Service on the date indicated above as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.

Certificate of Mailing via First Class Mail (1 page)
Amendment (8 pages)
Information Disclosure Statement (1 original & 1 copy)
IDS Form PTO/SB/08A with ten (10) references cited (1 page)
Copy of PCT International Search Report (4 pages)
Return Postcard

Respectfully submitted,

A handwritten signature in black ink.

Carrie Roth
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218